Please replace the paragraph beginning on page 4, line 2, with the following rewritten paragraph:

A2

According to a first aspect of the present invention, there is provided a solid-state imaging device having a light-receiving portion formed on a semiconductor substrate and a light-shielding film formed so as to cover an electrode formed on the semiconductor substrate at least on its regions other than a region above the light-receiving portion. This solid-state imaging device is arranged such that the light-shielding film has a multilayer structure including a first film formed of a film deposited by sputtering or vapor deposition and a second film deposited by chemical vapor deposition.--

Please replace the paragraph beginning on page 4, line 23, with the following rewritten paragraph:

A3

According to a third aspect of the present invention, there is provided a method of manufacturing a semiconductor device which comprises the steps of forming a first film on the surface of a substrate by sputtering or vapor deposition, removing a native oxide from the surface of the first film, forming a second film on the first film by chemical vapor deposition, and forming a conductive film of a mulitlayer film including the first film and the second film.

Please replace the paragraph beginning on page 5, line 4, with the following rewritten paragraph:

A4

According to the solid-state imaging device of the present invention, since the first film is formed of the film deposited by sputtering or vapor deposition, the first film has an excellent adhesion with the underlayer. Also, since the second film formed of the tungsten film deposited by chemical vapor

q4 end

deposition is formed on the first film, the second film is formed with an excellent adhesion through the first film, and a sufficient light-shielding property may be maintained by the second film.

Please replace the paragraph beginning on page 5, line 12, with the following rewritten paragraph:

q5

According to the method of manufacturing a solid-state imaging device of the present invention, since the first film is formed of the film deposited by sputtering or vapor deposition, the first film is deposited with an excellent adhesion with the underlayer. Also, since the second film formed of the tungsten film is formed on the first film, the second film is formed with an excellent adhesion through the first film. Also, since the second film is deposited by chemical vapor deposition, a step coverage is satisfactory and a leakage of light from a step side wall or the like may be prevented, thereby making is possible to maintain a sufficient light-shielding property.

Please replace the paragraph beginning on page 6, line 15, with the following rewritten paragraph:

q6

According to the present invention, there is provided a solid-state imaging device having a light-receiving portion formed on a semiconductor substrate and a light-shielding film formed so as to cover an electrode formed on the semiconductor substrate at least on its regions other than a region above the light-receiving portion. This solid-state imaging device is characterized in that the light-shielding film has a mulitlayer structure including a first film formed of a film deposited by sputtering or vapor deposition and a second film deposited by chemical vapor deposition.

Please replace the paragraph beginning on page 6, line 25, with the following rewritten paragraph:

Q7

According to the present invention, there is provided a method of manufacturing a solid-state imaging device which comprises the steps of forming a light-receiving portion on a semiconductor substrate, forming an electrode on the semiconductor substrate at least on its regions other than a region above the light-receiving portion, forming an insulating film on the electrode, and forming a light-receiving portion so as to cover the insulating film, wherein the light-shielding film is formed in such a manner that, after a first film is formed by sputtering or vapor deposition, a second film is formed on the first film by chemical vapor deposition.

Please replace the paragraph beginning on page 7, line 9, with the following rewritten paragraph:

Q8

According to the present invention, there is provided a method of manufacturing a semiconductor device which comprises the steps of forming a first film on the surface of a substrate by sputtering or vapor deposition, removing a natural oxide from the surface of the first film, forming a second film on the first film by chemical vapor deposition, and forming a conductive film of a multilayer film including the first film and the second film.

Please replace the paragraph beginning on page 11, line 10, with the following rewritten paragraph:

Q9

Incidentally, if the surface of the second film 12, i.e. the surface of the light-shielding film 6 is rough, then incident light is irregularly reflected on such rough surface so that a light-receiving amount of each pixel is fluctuated, thereby resulting in a fluctuating sensitivity.